

### NPN SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND MID-SPEED SWITCHING

#### FEATURES

- Large current capacitance in small dimension:  $I_{C(DC)} = 7\text{ A}$
- Low collector saturation voltage:  
 $V_{CE(sat)} = 0.3\text{ V MAX.}$  ( $I_C = 3.0\text{ A}$ )
- Ideal for use in a lamp driver
- Complementary transistor: 2SA1129

#### ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	100	V
Collector to emitter voltage	$V_{CEO}$	40	V
Emitter to base voltage	$V_{EBO}$	7.0	V
Collector current (DC)	$I_{C(DC)}$	7.0	A
Collector current (pulse)	$I_{C(pulse)}^*$	15	A
Base current (DC)	$I_{B(DC)}$	3.5	A
Total power dissipation	$P_T (T_c = 25^\circ\text{C})$	40	W
Total power dissipation	$P_T (T_a = 25^\circ\text{C})$	1.5	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\*  $PW \leq 300\ \mu\text{s}$ , duty cycle  $\leq 10\%$

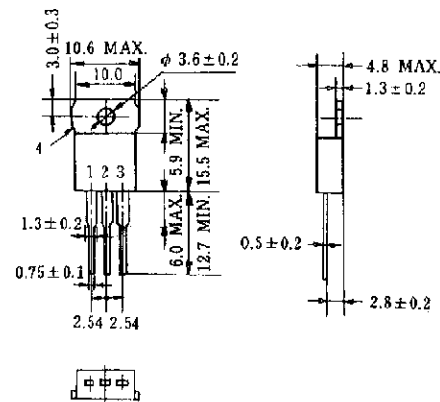
#### ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 40\text{ V}, I_E = 0$			10	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 5.0\text{ V}, I_C = 0$			10	$\mu\text{A}$
DC current gain	$h_{FE1}$	$V_{CE} = 1.0\text{ V}, I_C = 3\text{ A}^*$	40		320	
DC current gain	$h_{FE2}$	$V_{CE} = 1.0\text{ V}, I_C = 5\text{ A}^*$	20			
Collector saturation voltage	$V_{CE(sat)1}$	$I_C = 3.0\text{ A}, I_B = 0.1\text{ A}^*$			0.3	V
Base saturation voltage	$V_{BE(sat)1}$	$I_C = 3.0\text{ A}, I_B = 0.1\text{ A}^*$			1.5	V
Collector saturation voltage	$V_{CE(sat)2}$	$I_C = 5.0\text{ A}, I_B = 0.5\text{ A}^*$			0.6	V
Base saturation voltage	$V_{BE(sat)2}$	$I_C = 5.0\text{ A}, I_B = 0.5\text{ A}^*$			2.0	V
Turn-on time	$t_{on}$	$I_C = 5.0\text{ A}, I_{B1} = -I_{B2} = 0.5\text{ A}$			1.0	$\mu\text{s}$
Storage time	$t_{stg}$	$R_L = 4.0\ \Omega, V_{CC} \cong 20\text{ V}$			2.5	$\mu\text{s}$
Fall time	$t_f$	$PW \cong 50\ \mu\text{s}, \text{duty cycle} \leq 2\%$			1.0	$\mu\text{s}$

\* Pulse test  $PW \leq 350\ \mu\text{s}$ , duty cycle  $\leq 2\%$

$h_{FE1}$  classification M: 40 to 80, L: 60 to 120, K: 100 to 200, J: 160 to 320

#### PACKAGE DRAWING (UNIT: mm)



#### Electrode Connection

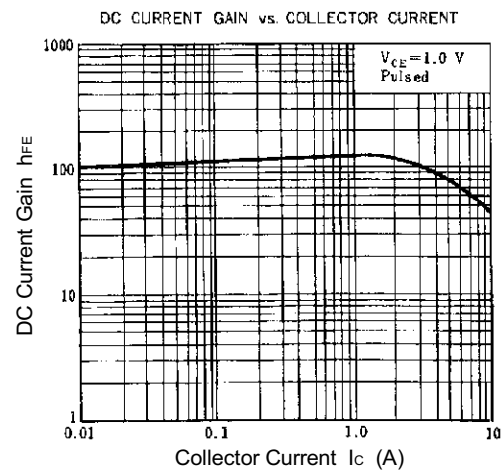
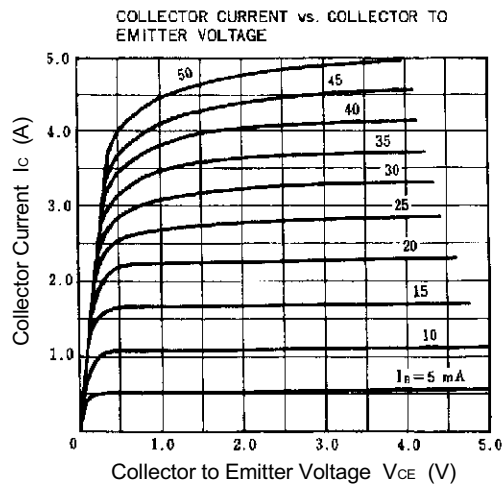
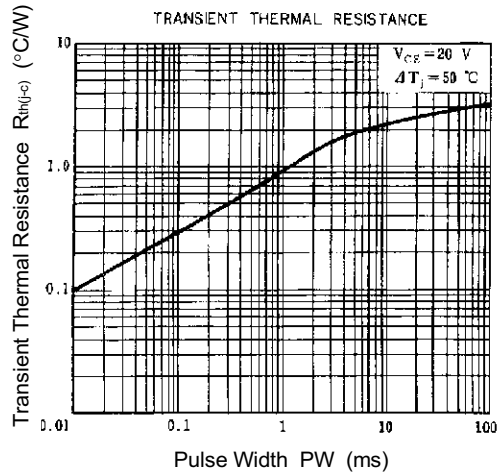
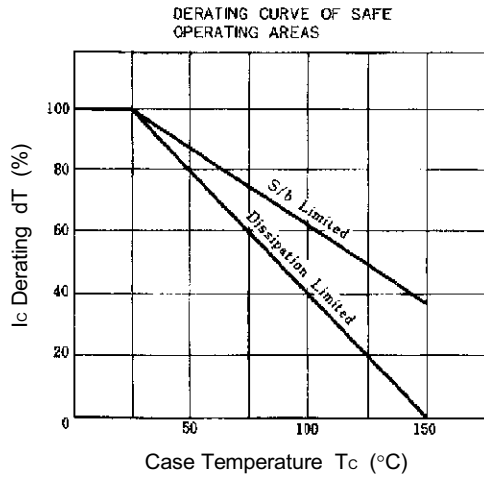
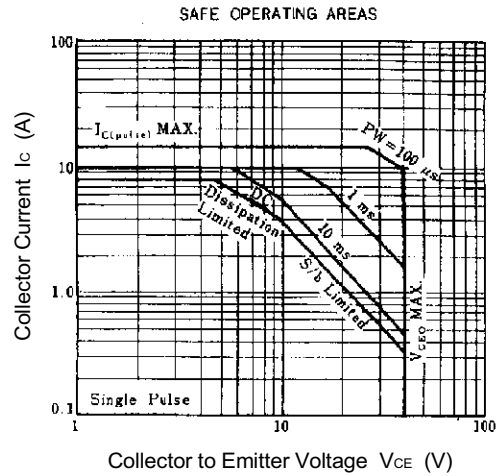
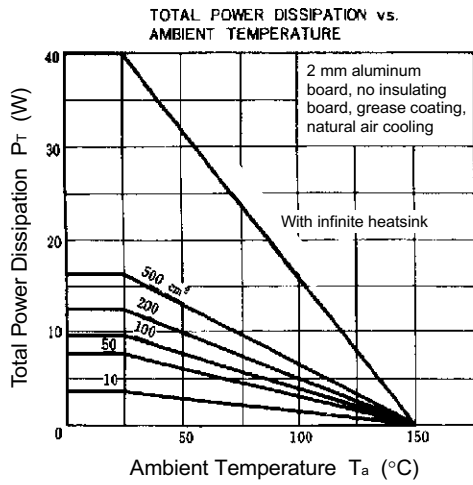
1. Base (B)
2. Collector (C)
3. Emitter (E)
4. Fin (Collector)

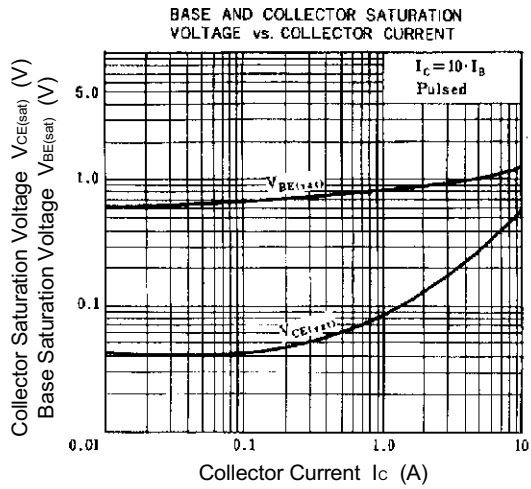
EIAJ : SC-46

JEDEC : TO-220AB

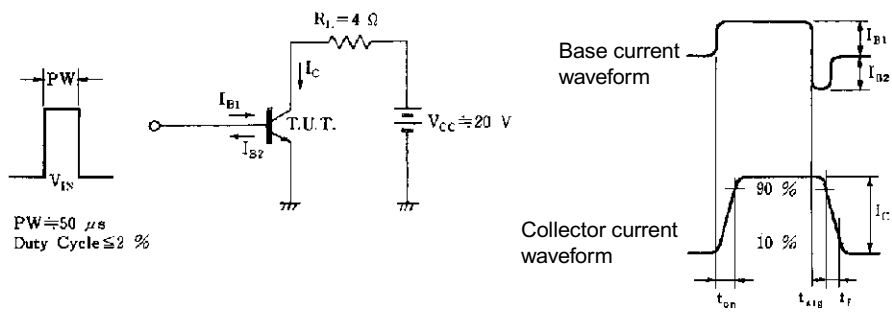
IEC : —

TYPICAL CHARACTERISTICS (Ta = 25°C)





**SWITCHING TIME ( $t_{on}$ ,  $t_{stg}$ ,  $t_f$ ) TEST CIRCUIT**



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